Description

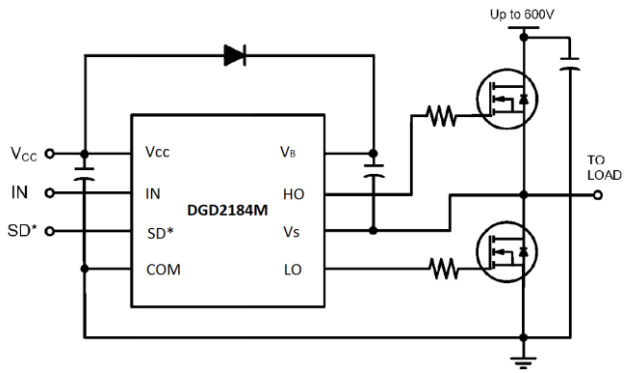
The DGD2184M is a high-voltage and high-speed gate driver capable of driving N-Channel MOSFETs and IGBTs in a half bridge configuration. High-voltage processing techniques enable the DGD2184M's high-side to switch to 600V in a bootstrap operation.

The DGD2184M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) for easy interfacing with controlling devices. The driver outputs feature high-pulse current buffers designed for minimum driver cross conduction. The DGD2184M has a fixed internal deadtime of 395ns (typ).

The DGD2184M is offered in the SO-8 (Type TH) package, and the operating temperature extends from -40°C to +125°C.

Applications

- DC-DC converters
- DC-AC inverters
- AC-DC power supplies
- Motor controls
- Class D power amplifiers



Typical Configuration

Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in Half Bridge Configuration
- 1.9A Source / 2.3A Sink Output Current Capability
- Outputs Tolerant to Negative Transients
- Internal Dead Time of 395ns to Protect MOSFETs
- Wide Low-Side Gate Driver and Logic Supply: 10V to 20V
- Logic Input (IN and SD*) 3.3V Capability
- Schmitt Triggered Logic Inputs with Internal Pull Down
- Undervoltage Lockout for High- and Low-Side Drivers
- Extended Temperature Range: -40°C to +125°C
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.**
  https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SO-8 (Type TH)
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.075 grams (Approximate)

SO-8

Top View

Ordering Information (Note 4)

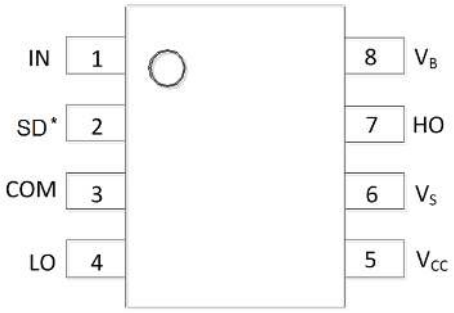
Orderable Part Number	Package	Marking	Reel Size (inch)	Tape Width (mm)	Packing	
					Qty.	Carrier
DGD2184MS8-13	SO-8 (Type TH)	DGD2184M	13	12	2,500	Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

= Manufacturer's Marking
DGD2184M = Product Type Marking Code
YY = Year (ex: 23 = 2023)
WW = Week (01 to 53)

Pin Diagrams

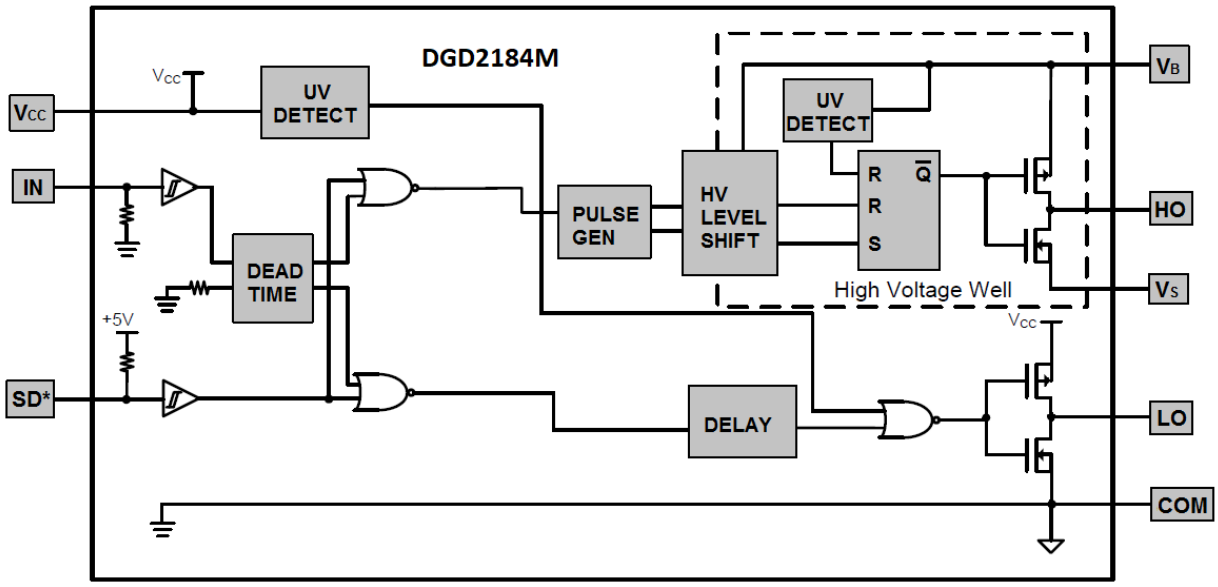


Top View SO-8

Pin Descriptions

Pin Number	Pin Name	Function
1	IN	Logic Input for High-Side and Low-Side Gate Driver Outputs (HO and LO), in Phase with HO
2	SD*	Logic Input for Shutdown, Enabled Low
3	COM	Low-Side and Logic Return
4	LO	Low-Side Gate Drive Output
5	V_{CC}	Low-Side and Logic Fixed Supply
6	V_S	High-Side Floating Supply Return
7	HO	High-Side Gate Drive Output
8	V_B	High-Side Floating Supply

Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	V_B	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	V_S	V_B – 24 to V_B + 0.3	V
High-Side Floating Output Voltage	V_{HO}	V_S – 0.3 to V_B + 0.3	V
Offset Supply Voltage Transient	dV_S / dt	50	V/ns
Low-Side Fixed Supply Voltage	V_{CC}	-0.3 to +24	V
Low-Side Output Voltage	V_{LO}	-0.3 to V_{CC} + 0.3	V
Logic Input Voltage (IN and SD*)	V_{IN}	-0.3 to V_{CC} + 0.3	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P_D	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	°C/W
Operating Temperature	T_J	+150	°C
Lead Temperature (Soldering, 10s)	T_L	+300	
Storage Temperature Range	T_{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply Absolute Voltage	V_B	V_S + 10	V_S + 20	V
High-Side Floating Supply Offset Voltage	V_S	(Note 6)	600	V
High-Side Floating Output Voltage	V_{HO}	V_S	V_B	V
Low-Side Fixed Supply Voltage	V_{CC}	10	20	V
Low-Side Output Voltage	V_{LO}	0	V_{CC}	V
Logic Input Voltage (IN and SD*)	V_{IN}	0	V_{CC}	V
Ambient Temperature	T_A	-40	+125	°C

Note: 6. Logic operation for V_S of -5V to +600V.

DC Electrical Characteristics (V_{BIAS} (V_{CC}, V_{BS}) = 15V, @T_A = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Logic "1" Input Voltage	V_{IH}	2.5	—	—	V	V_{CC} = 10V to 20V
Logic "0" Input Voltage	V_{IL}	—	—	0.8	V	V_{CC} = 10V to 20V
SD* Input Positive Going Threshold	V_{SDTH+}	2.5	—	—	V	V_{CC} = 10V to 20V
SD* Input Negative Going Threshold	V_{SDTH-}	—	—	0.8	V	V_{CC} = 10V to 20V
High Level Output Voltage, V_{BIAS} – V_O	V_{OH}	—	—	1.2	V	I_O = 0mA
Low Level Output Voltage, V_O	V_{OL}	—	—	0.1	V	I_O = 20mA
Offset Supply Leakage Current	I_{LK}	—	—	50	µA	V_B = V_S = 600V
Quiescent V_{BS} Supply Current	I_{BSQ}	20	60	150	µA	V_{IN} = 0V or 5V
Quiescent V_{CC} Supply Current	I_{CCQ}	0.4	1.0	1.8	mA	V_{IN} = 0V or 5V
Logic "1" Input Bias Current	I_{IN+}	—	25	60	µA	IN = 5V, SD* = 0V
Logic "0" Input Bias Current	I_{IN-}	—	—	1.0	µA	IN = 0V, SD* = 5V
V_{BS} Supply Under-Voltage Positive Going Threshold	V_{BSUV+}	8.0	8.9	9.8	V	—
V_{BS} Supply Under-Voltage Negative Going Threshold	V_{BSUV-}	7.4	8.2	9.0	V	—
V_{CC} Supply Under-Voltage Positive Going Threshold	V_{CCUV+}	8.0	8.9	9.8	V	—
V_{CC} Supply Under-Voltage Negative Going Threshold	V_{CCUV-}	7.4	8.2	9.0	V	—
Output High Short Circuit Pulsed Current	I_{O+}	1.4	1.9	—	A	V_O = 0V, PW ≤ 10µs
Output Low Short Circuit Pulsed Current	I_{O-}	1.7	2.3	—	A	V_O = 15V, PW ≤ 10µs

Note: 7. The V_{IN} and I_{IN} parameters are applicable to the two logic input pins: IN and SD*. The V_O and I_O parameters are applicable to the respective output pins: HO and LO.

AC Electrical Characteristics (V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000pF, @T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Turn-On Propagation Delay	t_{on}	—	585	900	ns	V_S = 0V
Turn-Off Propagation Delay	t_{off}	—	170	400	ns	V_S = 0V or 600V
Shut-Down Propagation Delay	t_{SD}	—	180	270	ns	—
Delay Matching, HO & LO Turn-On	t_{DMON}	—	—	90	ns	—
Delay Matching, HO & LO Turn-Off	t_{DMOFF}	—	—	40	ns	I_O = 0A
Turn-On Rise Time	t_r	—	40	60	ns	V_S = 0V
Turn-Off Fall Time	t_f	—	20	35	ns	V_S = 0V
Deadtime: $t_{DT\ LO\text{-}HO}$ & $t_{DT\ HO\text{-}LO}$	t_{DT}	345	395	445	ns	—

Timing Waveforms

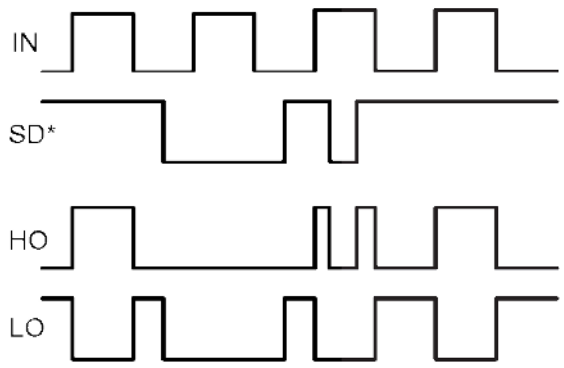


Figure 1. Input / Output Timing Diagram

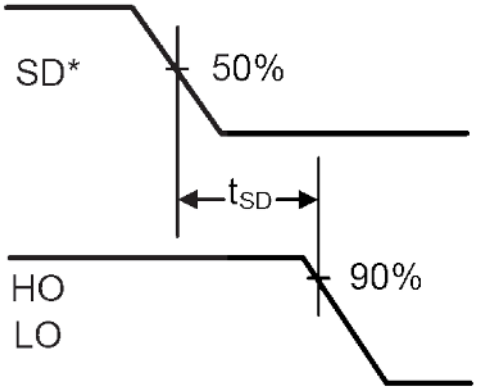
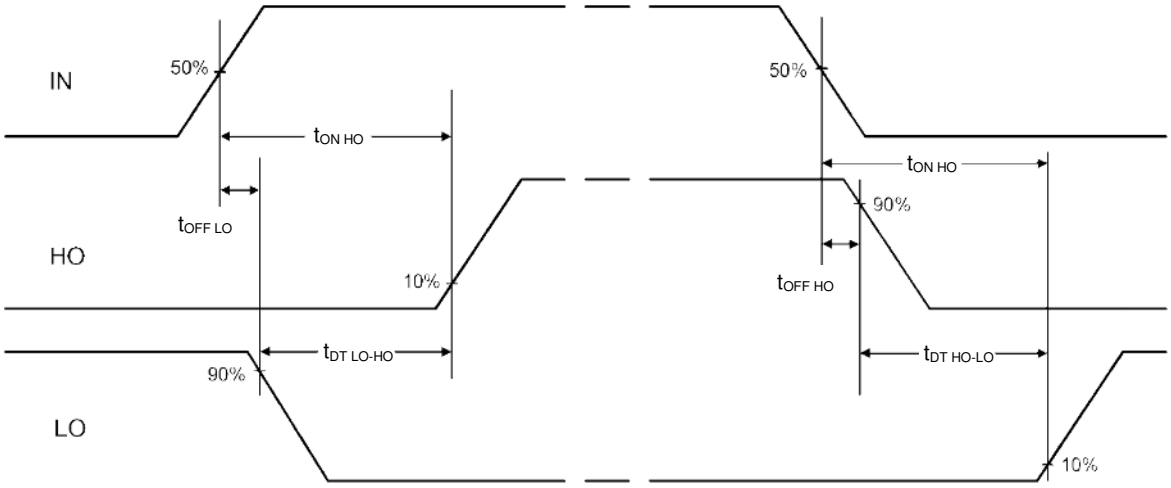


Figure 2. Shutdown Waveform Definitions



Deadtime $t_{DT\ LO-HO} = t_{ON\ HO} - t_{OFF\ LO}$

$t_{DT\ HO-LO} = t_{ON\ LO} - t_{OFF\ HO}$

Deadtime matching

$t_{MDT} = t_{DT\ LO-HO} - t_{DT\ HO-LO}$

Delay matching

$t_{DM\ OFF} = t_{OFF\ LO} - t_{OFFT\ HO}$

Figure 3. Switching Time Waveform Definitions

Typical Performance Characteristics (@T_A = +25°C, V_{CC} = 15V, unless otherwise specified.)

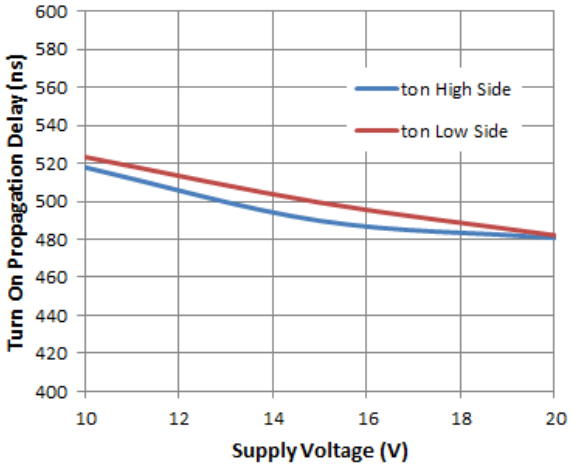


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

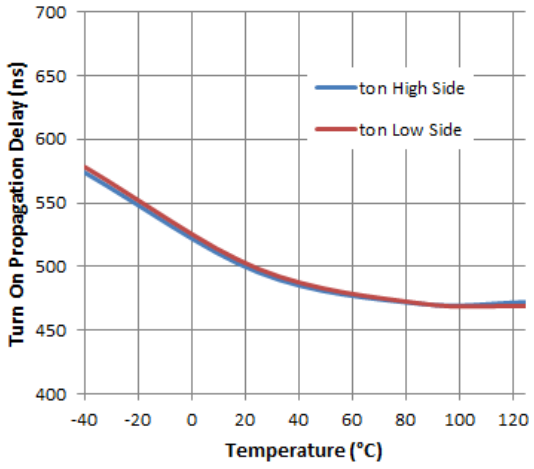


Figure 5. Turn-on Propagation Delay vs. Temperature

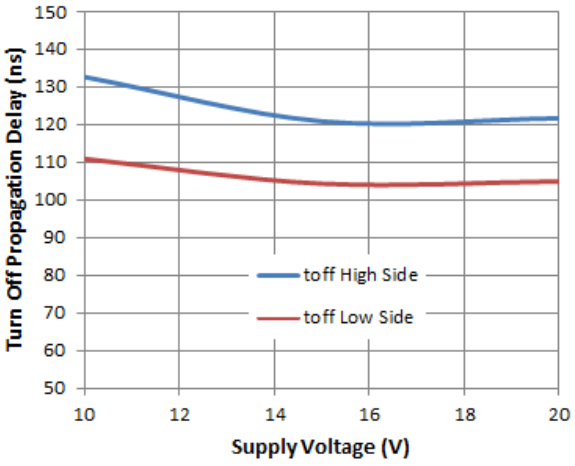


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

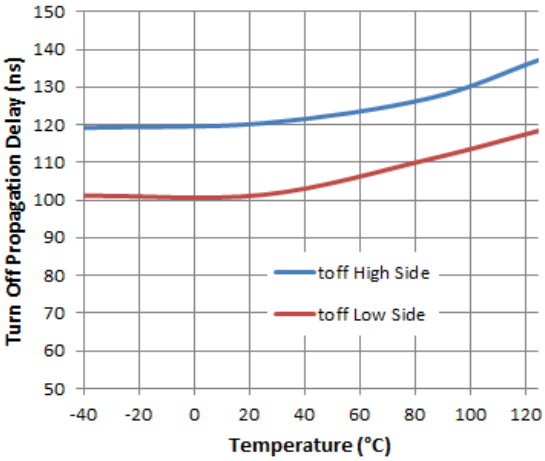


Figure 7. Turn-off Propagation Delay vs. Temperature

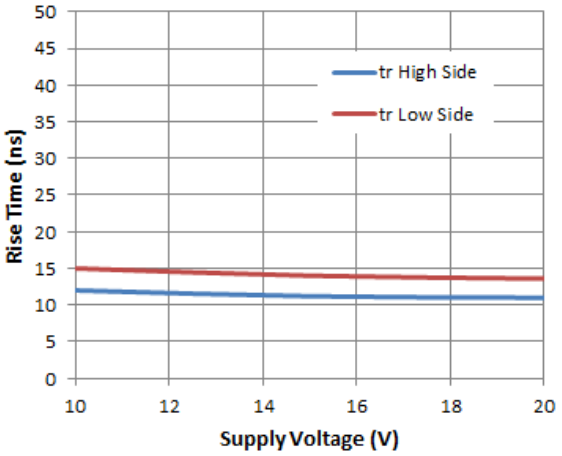


Figure 8. Rise Time vs. Supply Voltage

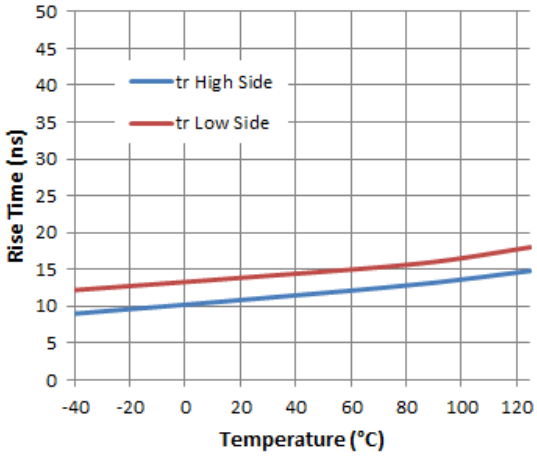


Figure 9. Rise Time vs. Temperature

Typical Performance Characteristics (continued)

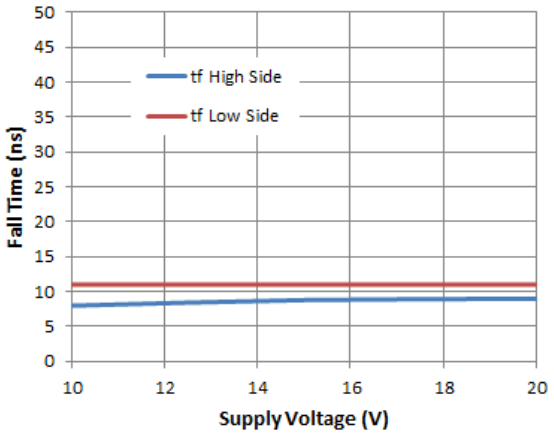


Figure 10. Fall Time vs. Supply Voltage

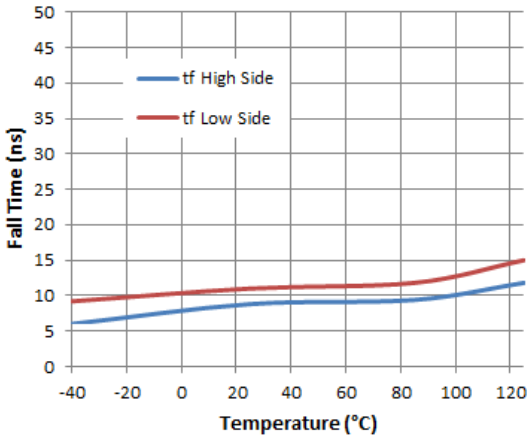


Figure 11. Fall Time vs. Temperature

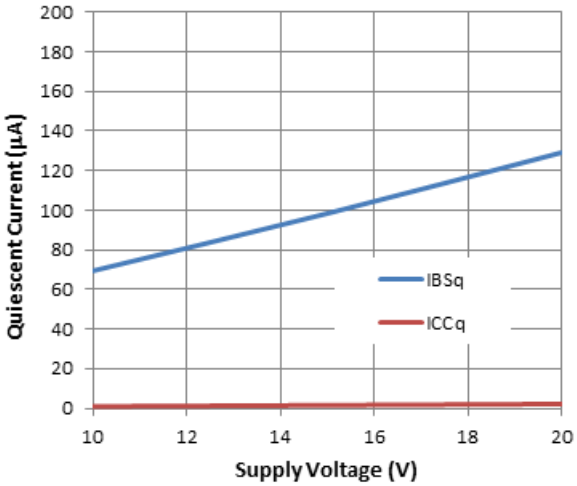


Figure 12. Quiescent Current vs. Supply Voltage

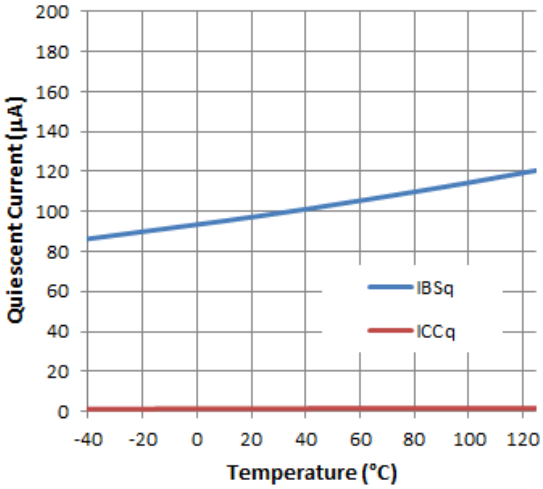


Figure 13. Quiescent Current vs. Temperature

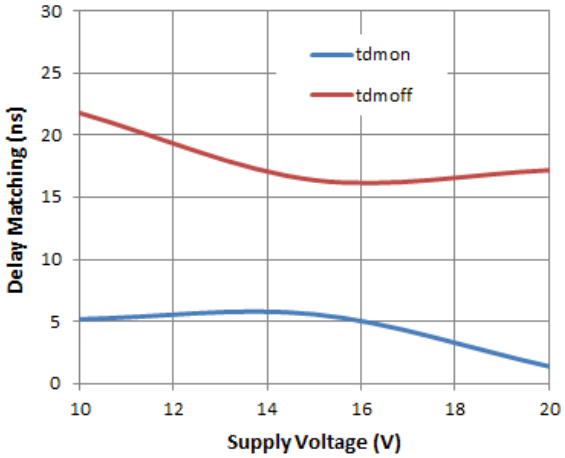


Figure 14. Delay Matching vs. Supply Voltage

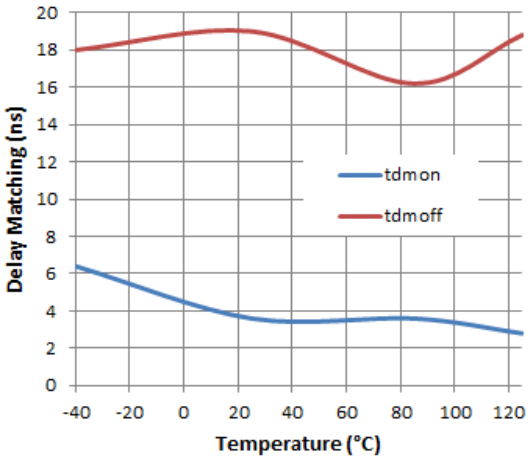


Figure 15. Delay Matching vs. Temperature

Typical Performance Characteristics (continued)

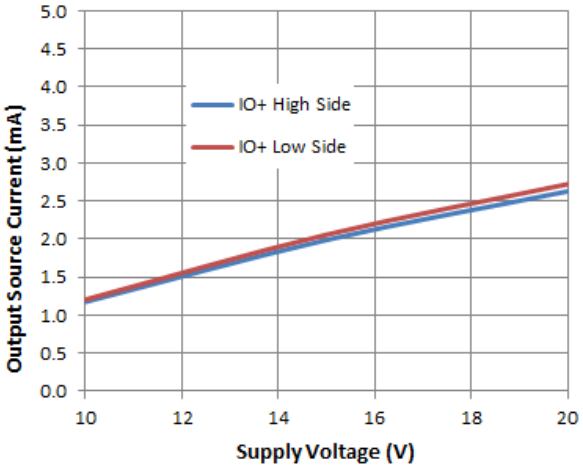


Figure 16. Output Source Current vs. Supply Voltage

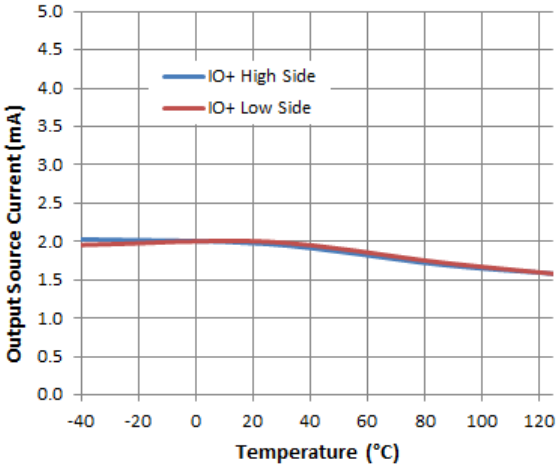


Figure 17. Output Source Current vs. Temperature

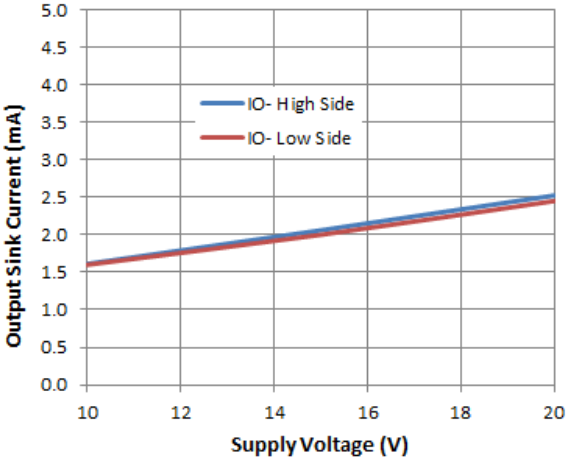


Figure 18. Output Sink Current vs. Supply Voltage

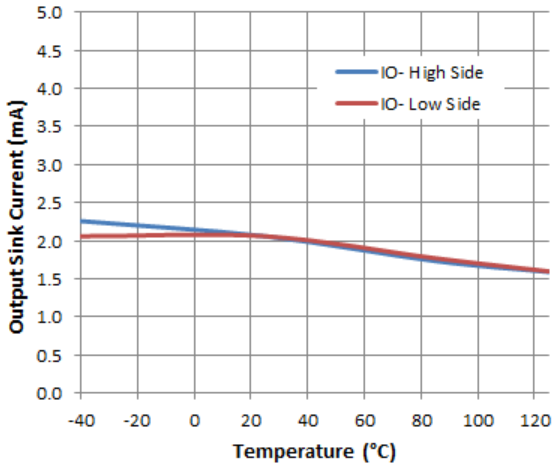


Figure 19. Output Sink Current vs. Temperature

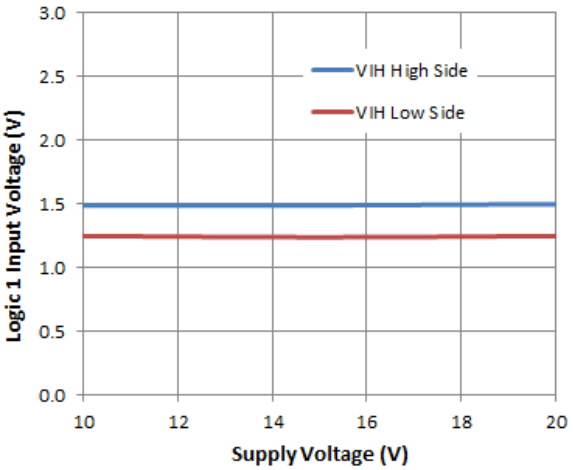


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

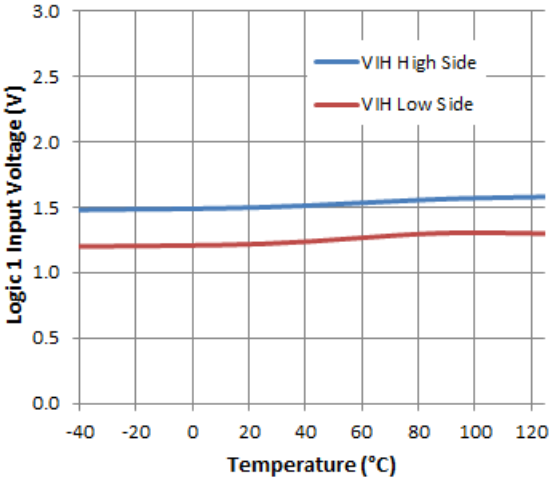


Figure 21. Logic 1 Input Voltage vs. Temperature

Typical Performance Characteristics (continued)

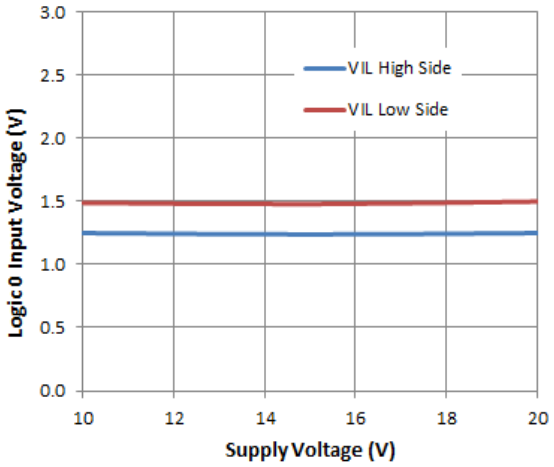


Figure 22. Logic 0 Input Voltage vs. Supply Voltage

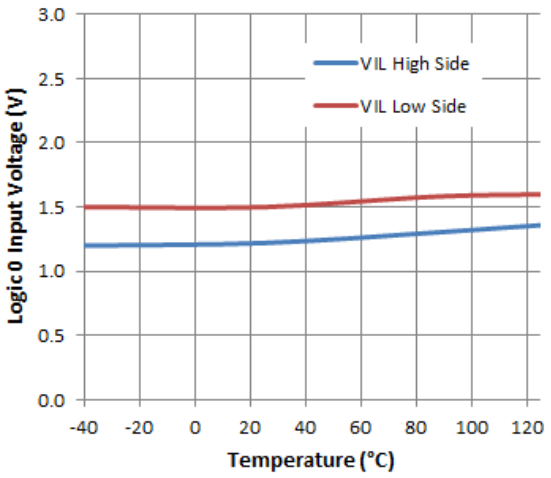


Figure 23. Logic 0 Input Voltage vs. Temperature

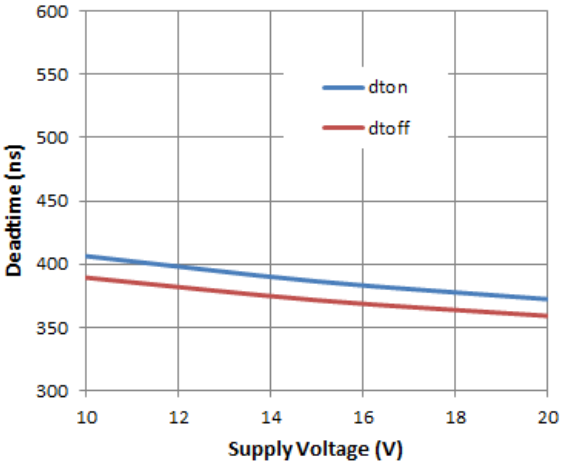


Figure 24. Deadtime vs. Supply Voltage

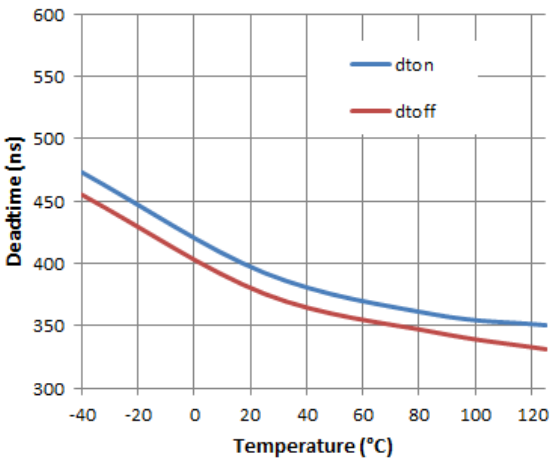


Figure 25. Deadtime vs. Temperature

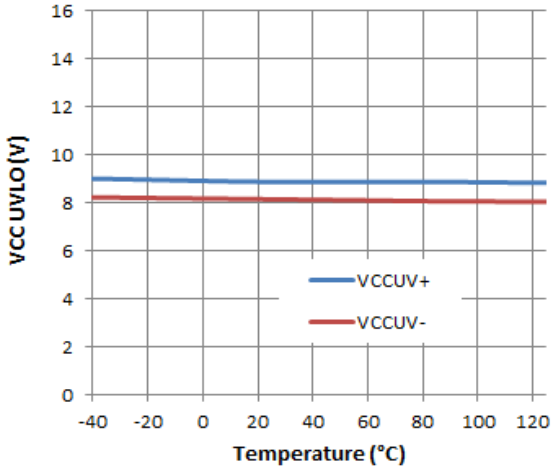


Figure 26. VCC UVLO vs. Temperature

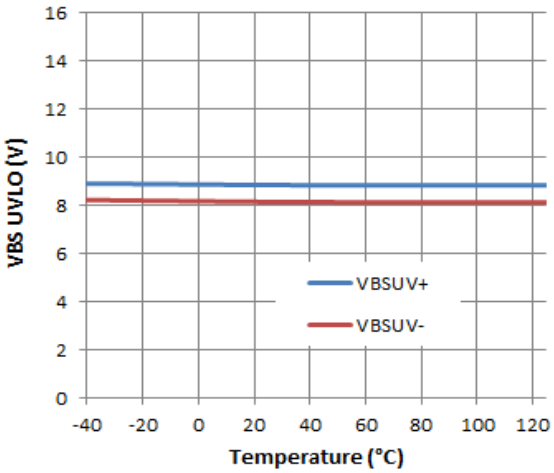


Figure 27. VBS UVLO vs. Temperature

Typical Performance Characteristics (continued)

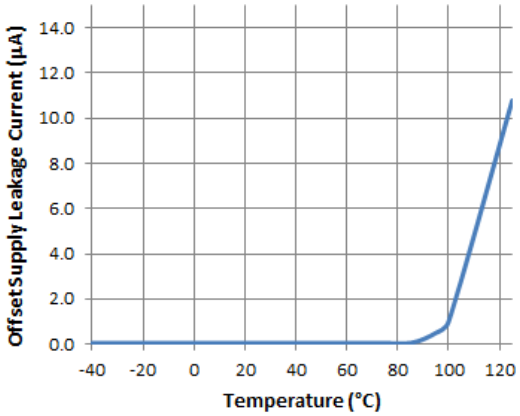
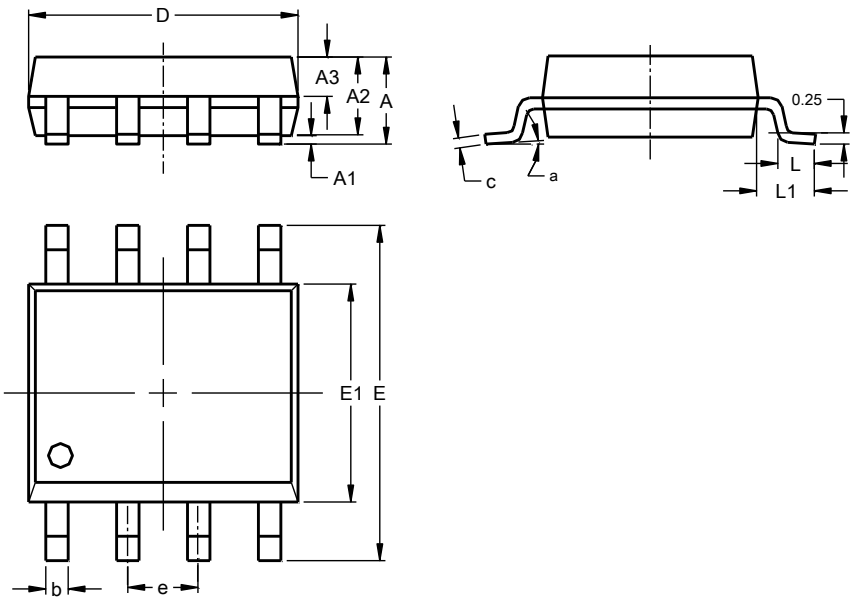


Figure 28. Offset Supply Leakage Current vs. Temperature

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8 (Type TH)

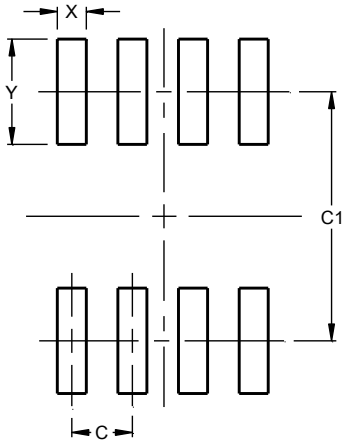


SO-8 (Type TH)			
Dim	**Min**	**Max**	**Typ**
A	--	1.75	--
A1	0.10	0.225	--
A2	1.30	1.50	1.40
A3	0.60	0.70	0.65
b	0.39	0.47	--
c	0.20	0.24	--
D	4.80	5.00	4.90
E	5.80	6.20	6.00
E1	3.80	4.00	3.90
e	1.27BSC		
h	0.25	0.50	--
L	0.50	0.80	--
L1	1.05REF		
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8 (Type TH)



Dimensions	Value (in mm)
C	1.27
C1	5.20
X	0.60
Y	2.20

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